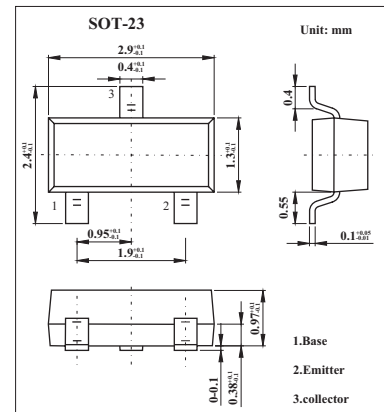


NPN General Purpose Transistors

BCF32

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 32 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	32	V
Collector-emitter voltage	V_{CE0}	32	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	100	mA
Peak collector current	I_{CM}	200	mA
Peak base current	I_{BM}	100	mA
Total power dissipation *	P_{tot}	250	mW
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	R_{amb}	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th\ j-a}$	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BCF32■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$I_E = 0; V_{CB} = 32\text{ V}$			100	nA
	I_{CBO}	$I_E = 0; V_{CB} = 32\text{ V}; T_j = 100^\circ\text{C}$			10	μA
Emitter cutoff current	I_{EBO}	$I_C = 0; V_{EB} = 5\text{ V}$			100	nA
DC current gain	h_{FE}	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$		150		
		$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$		120	250	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$		210		mV
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$		750		mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$		850		mV
Base to emitter voltage	V_{BE}	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	550		700	mV
Collector capacitance	C_C	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$		2.5		pF
Transition frequency	f_T	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100			MHz
Noise figure	NF	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$		1.2	4	dB

■ Marking

Marking	D7
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